

Designing Flexible Quantum Spin Hall Insulators through 2D Ordered Hybrid Transition Metal Carbides

*Zhongheng Fu,^{1,2} Zhaorui Liu,^{1,2} Dominik Legut,³ Timothy C. Germann,⁴ Chen Si,^{1,2} Shiyu Du,⁵
Joseph S. Francisco,⁶ and Ruifeng Zhang^{1,2,*}*

¹School of Materials Science and Engineering, Beihang University, Beijing 100191, P. R. China

*²Center for Integrated Computational Materials Engineering (International Research Institute
for Multidisciplinary Science) and Key Laboratory of High-Temperature Structural Materials &
Coatings Technology (Ministry of Industry and Information Technology), Beihang University,
Beijing 100191, P. R. China*

³IT4Innovations, VSB-Technical University of Ostrava, CZ-70800 Ostrava, Czech Republic

*⁴Theoretical Division, Los Alamos National Laboratory, Los Alamos, New Mexico, 87545,
United States*

*⁵Engineering Laboratory of Specialty Fibers and Nuclear Energy Materials, Ningbo Institute of
Materials Technology and Engineering, Chinese Academy of Sciences, Ningbo, Zhejiang,
315201, P. R. China*

⁶Department of Earth and Environmental Science and Department of Chemistry, University of Pennsylvania, Philadelphia, PA, 19104, United States

Table S1. Total energies in eV/atom of $M''_2M'C_2O_2$ in different configurations. The total energies of the most stable configurations are set as zero energy.

	configuration I	configuration II	configuration III
$Mo_2TiC_2O_2$	0.17	0.00	0.09
$W_2TiC_2O_2$	0.18	0.00	0.10
$Mo_2ZrC_2O_2$	0.14	0.00	0.07
$W_2ZrC_2O_2$	0.14	0.00	0.08
$Mo_2HfC_2O_2$	0.15	0.00	0.08
$W_2HfC_2O_2$	0.16	0.00	0.09

Table S2. Band gaps in eV of selected $M''_2M'C_2O_2$ for the test of U values of GGA + U . Note that the SOC interaction is considered in the related calculations.

U (eV)	$Mo_2TiC_2O_2$	$W_2HfC_2O_2$
0	0.04	0.28
1	0.05	0.29
2	0.06	0.31
3	0.08	0.34
4	0.11	0.38
5	0.15	0.45

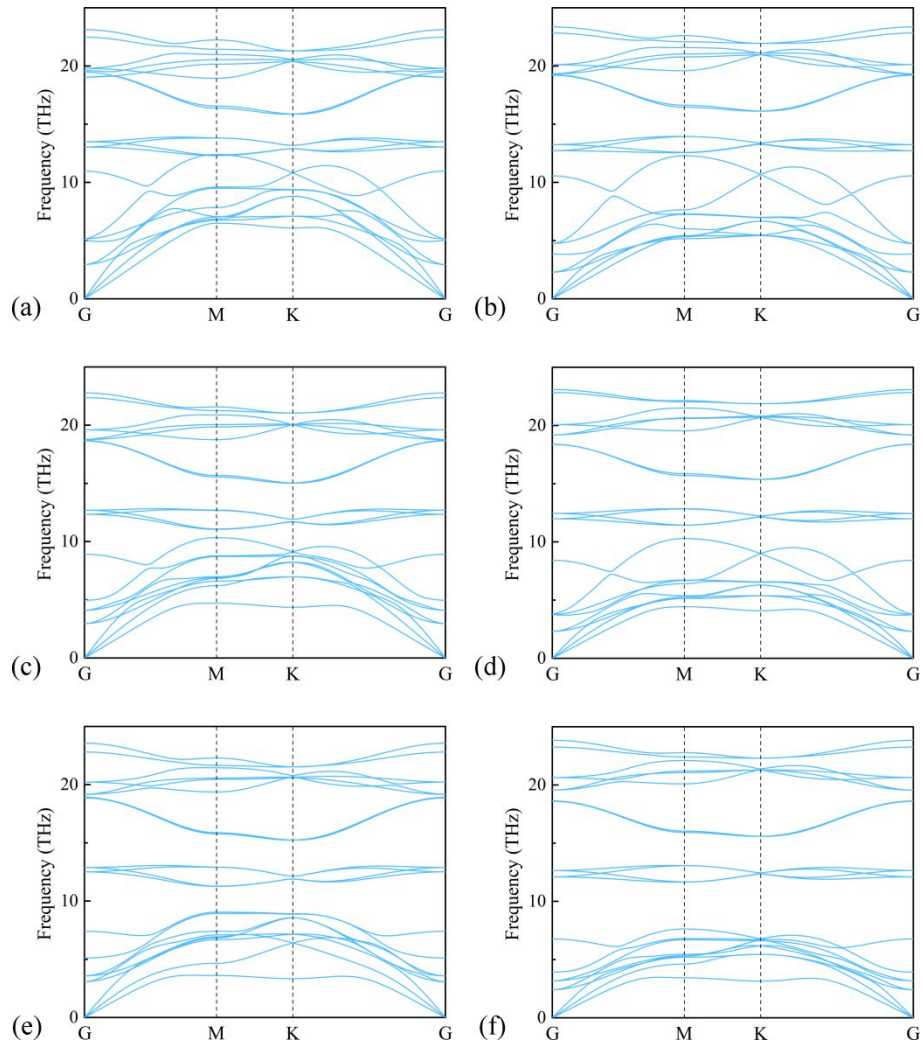


Figure S1. Phonon dispersions of (a) $\text{Mo}_2\text{TiC}_2\text{O}_2$, (b) $\text{W}_2\text{TiC}_2\text{O}_2$, (c) $\text{Mo}_2\text{ZrC}_2\text{O}_2$, (d) $\text{W}_2\text{ZrC}_2\text{O}_2$, (e) $\text{Mo}_2\text{HfC}_2\text{O}_2$, and (f) $\text{W}_2\text{HfC}_2\text{O}_2$.

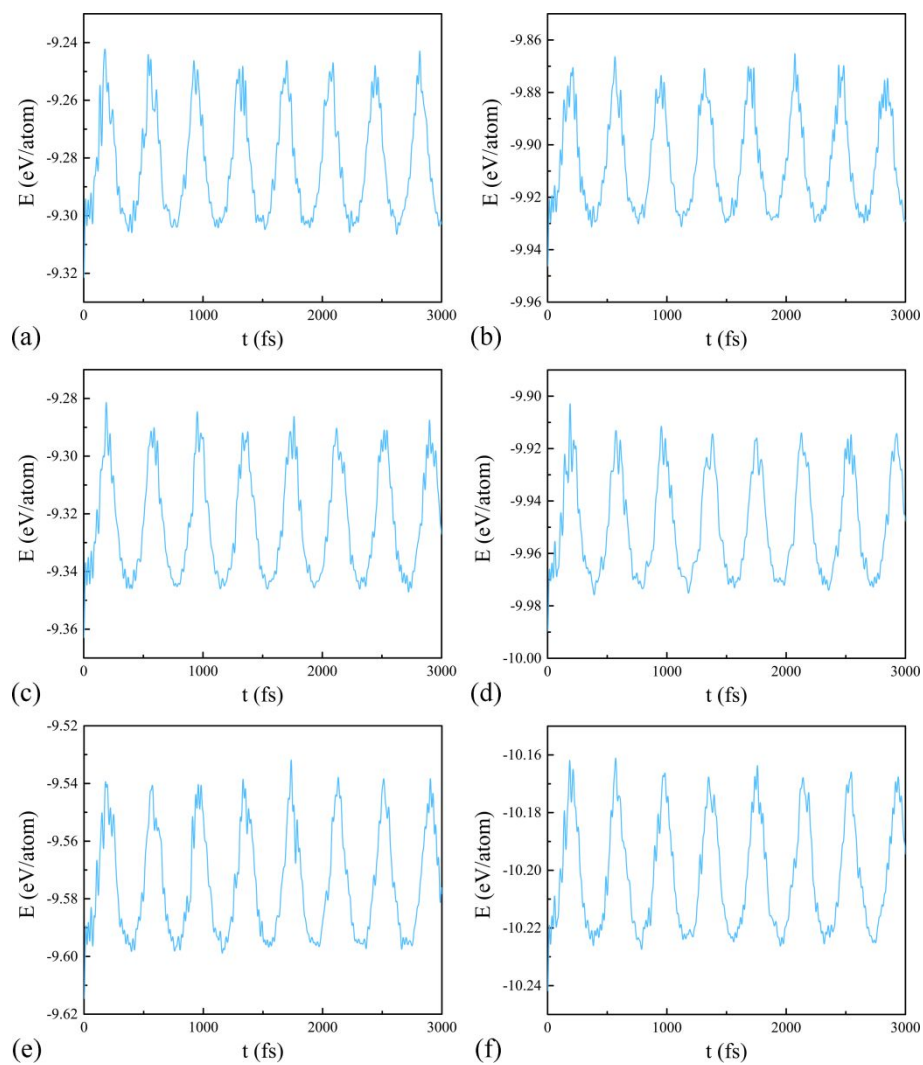


Figure S2. Variation of total energy during AIMD simulation at 300 K for (a) $\text{Mo}_2\text{TiC}_2\text{O}_2$, (b) $\text{W}_2\text{TiC}_2\text{O}_2$, (c) $\text{Mo}_2\text{ZrC}_2\text{O}_2$, (d) $\text{W}_2\text{ZrC}_2\text{O}_2$, (e) $\text{Mo}_2\text{HfC}_2\text{O}_2$, and (f) $\text{W}_2\text{HfC}_2\text{O}_2$.

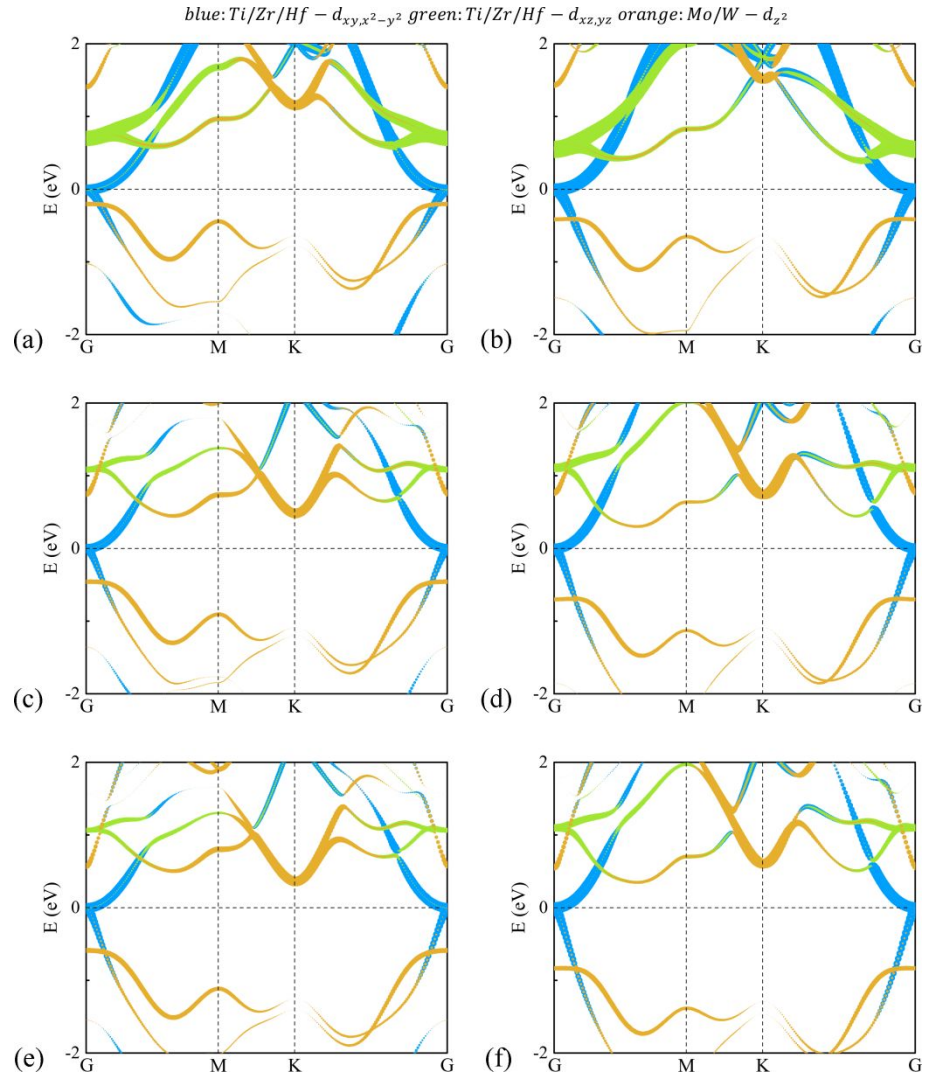


Figure S3. Projected band structures of (a) $\text{Mo}_2\text{TiC}_2\text{O}_2$, (b) $\text{W}_2\text{TiC}_2\text{O}_2$, (c) $\text{Mo}_2\text{ZrC}_2\text{O}_2$, (d) $\text{W}_2\text{ZrC}_2\text{O}_2$, (e) $\text{Mo}_2\text{HfC}_2\text{O}_2$, and (f) $\text{W}_2\text{HfC}_2\text{O}_2$ in GGA. The Fermi level is set to zero energy.

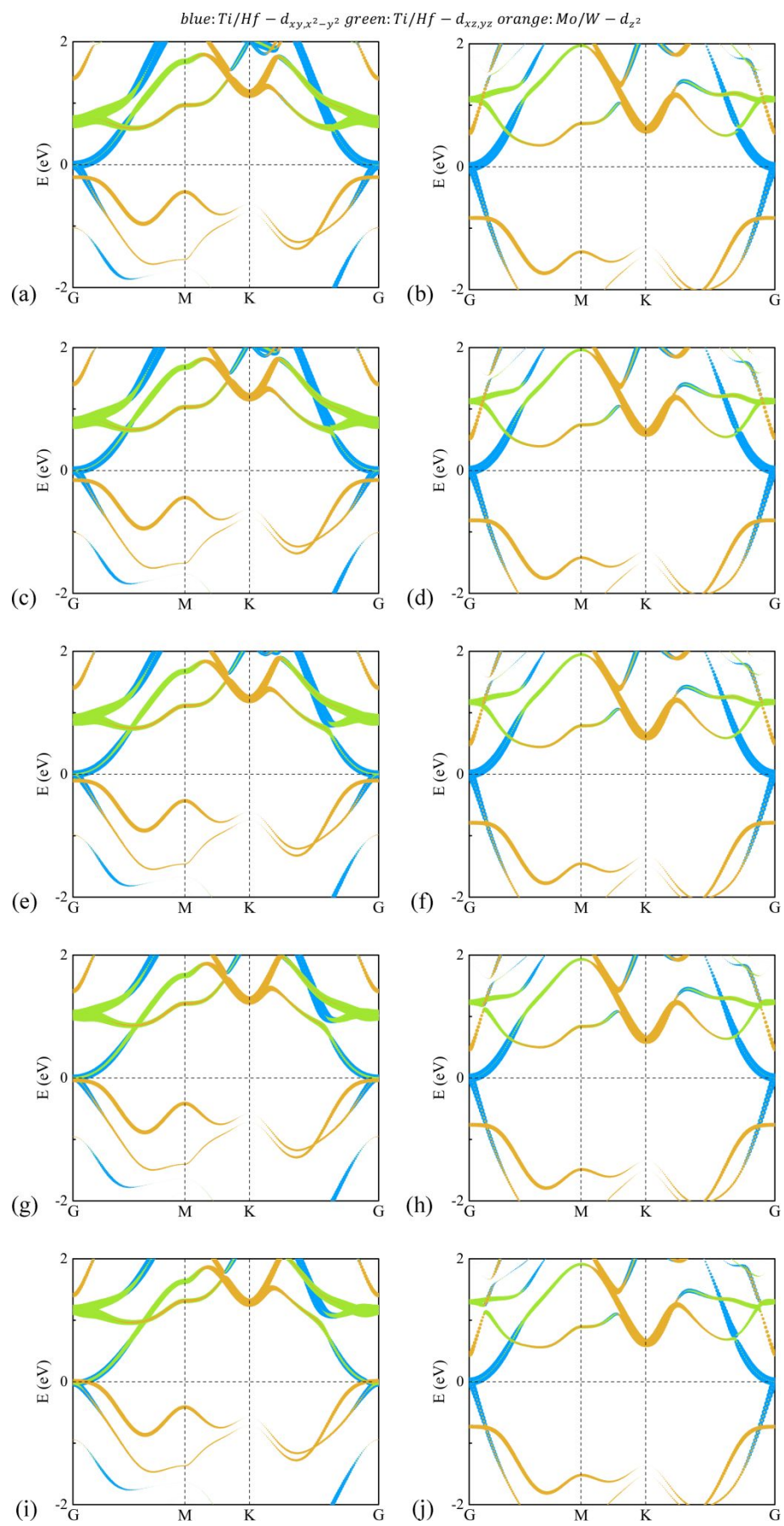


Figure S4. Projected band structures of $\text{Mo}_2\text{TiC}_2\text{O}_2$ in GGA + U , where (a) $U = 0$ eV, (c) $U = 1$ eV, (e) $U = 2$ eV, (g) $U = 3$ eV, and (i) $U = 4$ eV. Projected band structures of $\text{W}_2\text{HfC}_2\text{O}_2$ in GGA + U , where (b) $U = 0$ eV, (d) $U = 1$ eV, (f) $U = 2$ eV, (h) $U = 3$ eV, and (j) $U = 4$ eV. The Fermi level is set to zero energy.

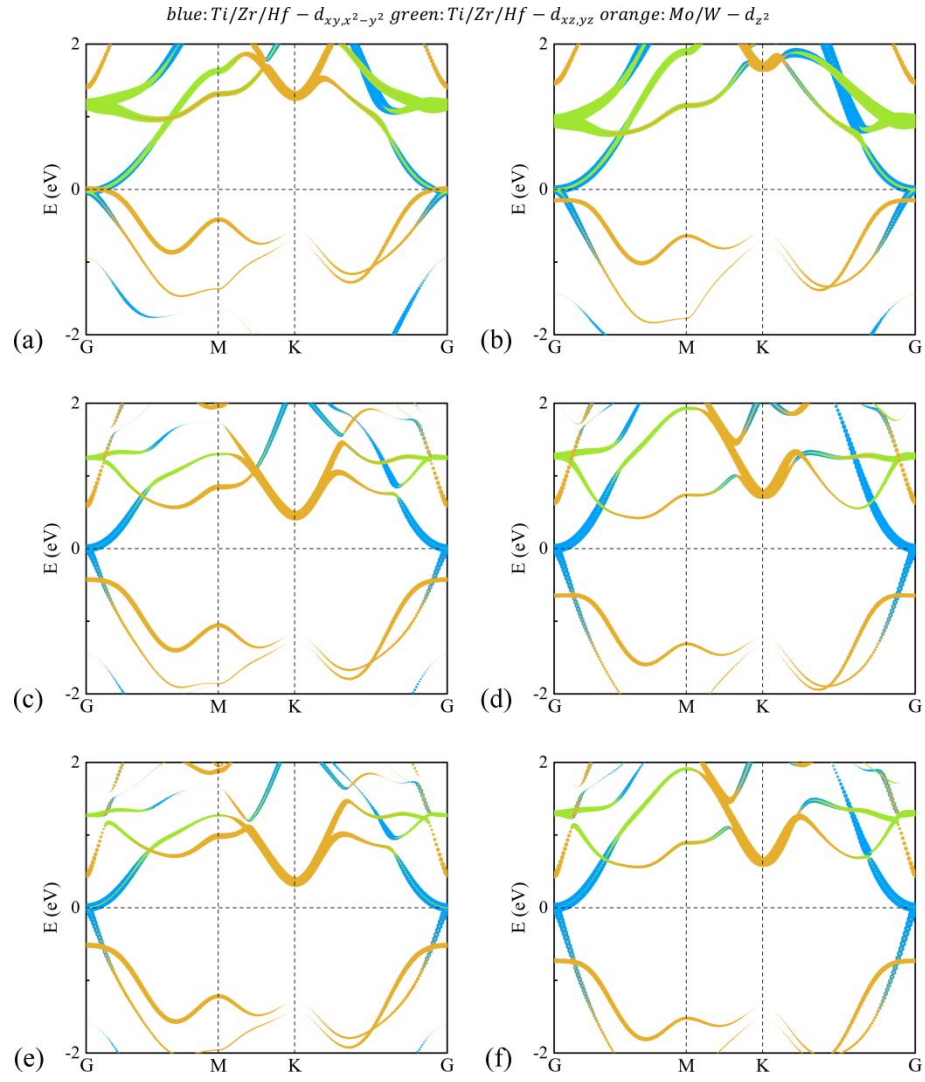


Figure S5. Projected band structures of (a) $\text{Mo}_2\text{TiC}_2\text{O}_2$, (b) $\text{W}_2\text{TiC}_2\text{O}_2$, (c) $\text{Mo}_2\text{ZrC}_2\text{O}_2$, (d) $\text{W}_2\text{ZrC}_2\text{O}_2$, (e) $\text{Mo}_2\text{HfC}_2\text{O}_2$, and (f) $\text{W}_2\text{HfC}_2\text{O}_2$ in GGA + U ($U = 4$ eV). The Fermi level is set to zero energy.

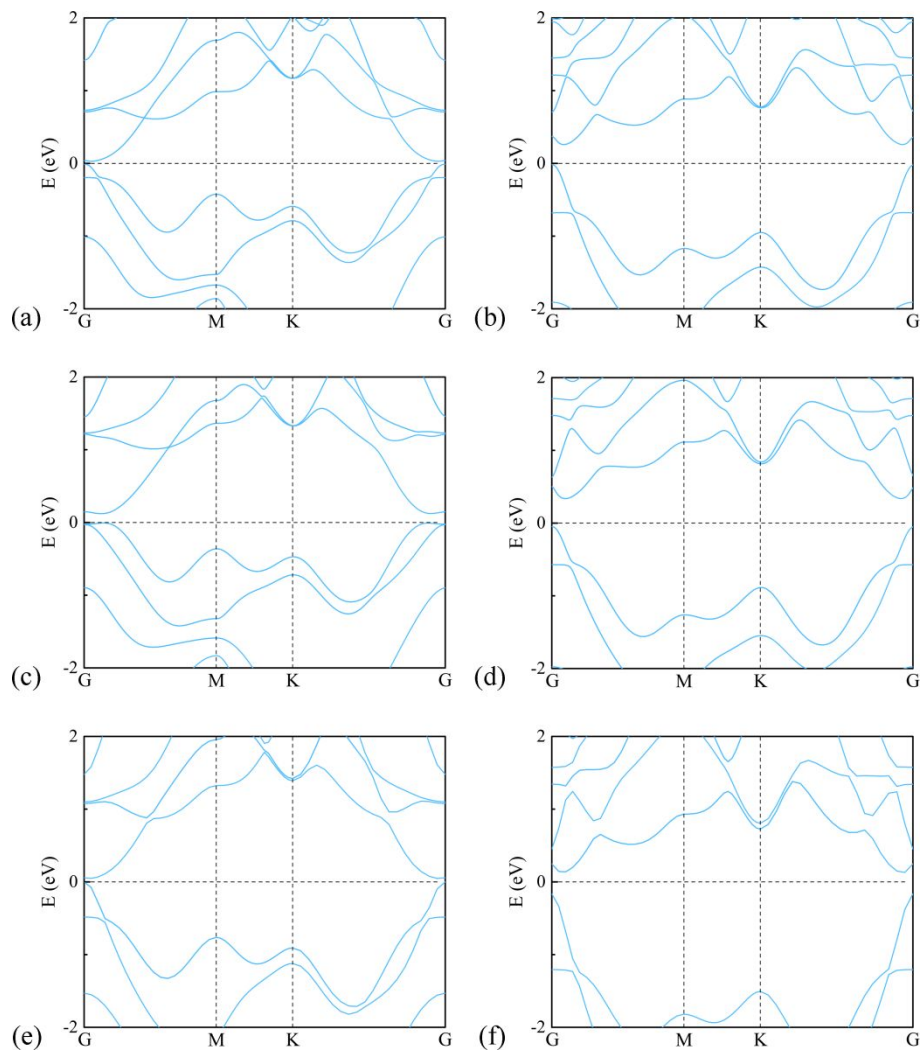


Figure S6. Electronic band structures of $\text{Mo}_2\text{TiC}_2\text{O}_2$ in (a) GGA, (c) GGA+ U ($U = 4$ eV), and (e) HSE. Electronic band structures of $\text{W}_2\text{HfC}_2\text{O}_2$ in (b) GGA, (d) GGA+ U ($U = 4$ eV), and (f) HSE. The SOC interaction is considered in the calculation of the band structures. The Fermi level is set to zero energy.

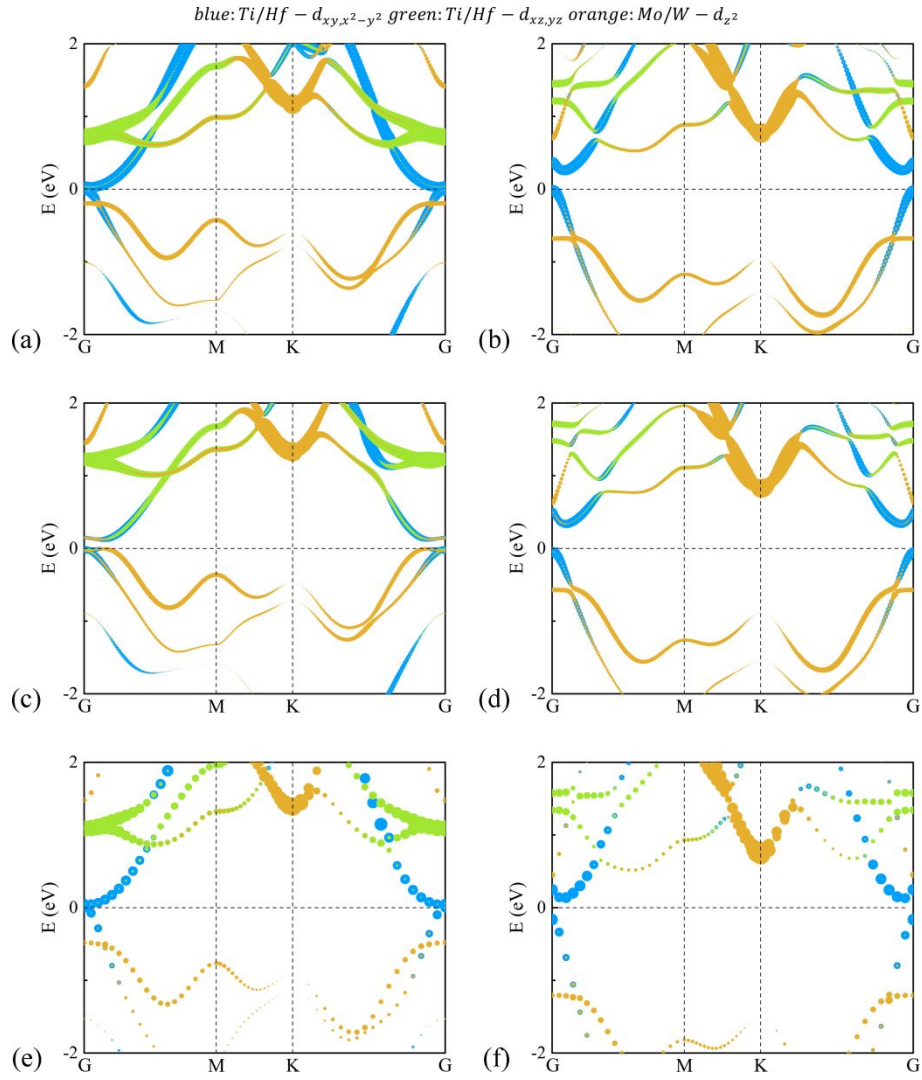


Figure S7. Projected band structures of $\text{Mo}_2\text{TiC}_2\text{O}_2$ in (a) GGA, (c) GGA+ U ($U = 4$ eV), and (e) HSE. Projected band structures of $\text{W}_2\text{HfC}_2\text{O}_2$ in (b) GGA, (d) GGA+ U ($U = 4$ eV), and (f) HSE. The SOC interaction is considered in the calculation of the band structures. The Fermi level is set to zero energy.

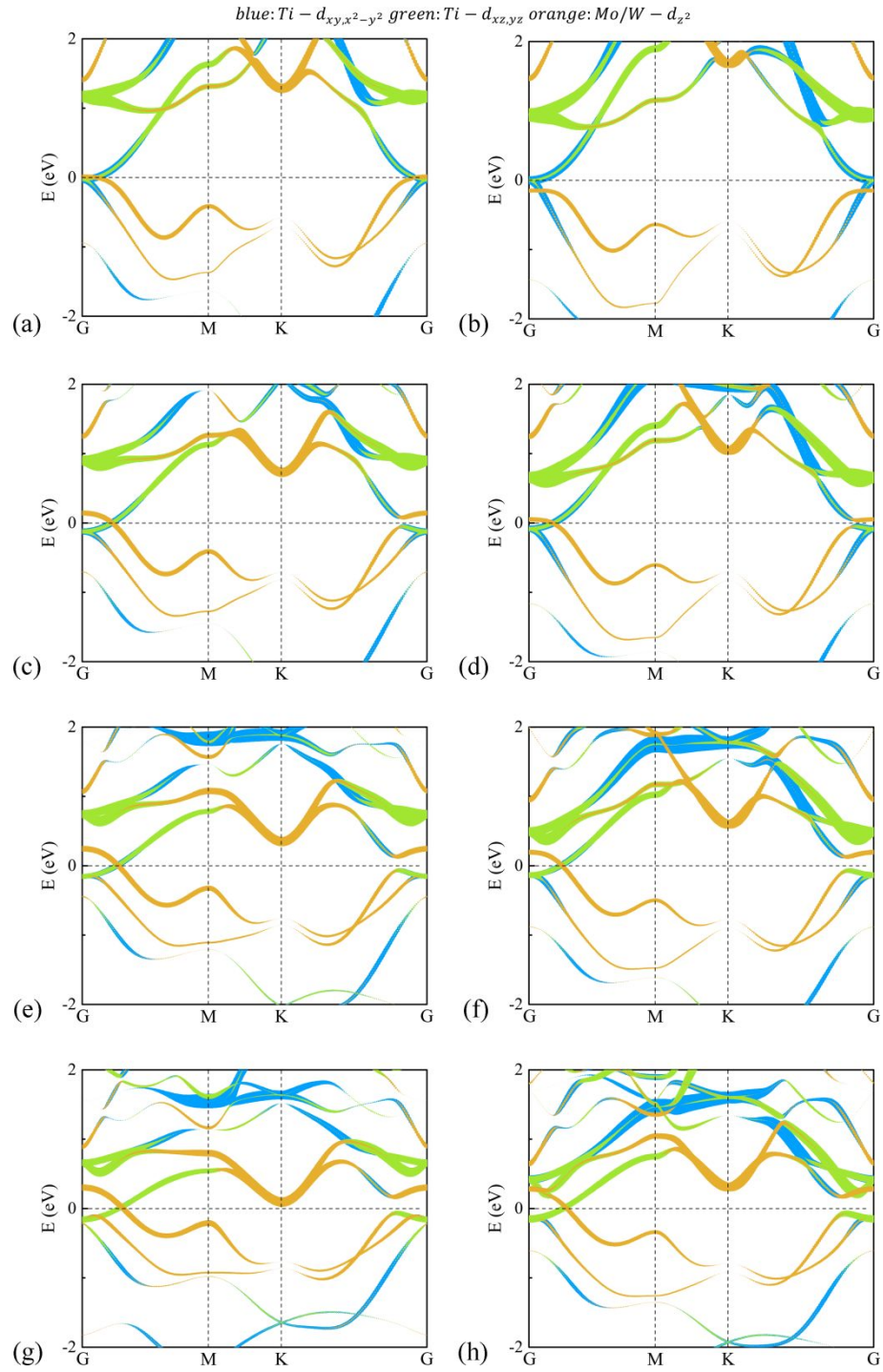


Figure S8. Projected band structures of $\text{Mo}_2\text{TiC}_2\text{O}_2$ (a) in equilibrium, (c) at strain $\varepsilon = 5\%$, (e) at strain $\varepsilon = 10\%$, and (g) at strain $\varepsilon = 15\%$. Projected band structures of $\text{W}_2\text{TiC}_2\text{O}_2$ (b) in equilibrium, (d) at strain $\varepsilon = 5\%$, (f) at strain $\varepsilon = 10\%$, and (h) at strain $\varepsilon = 15\%$. The Fermi level is set to zero energy.

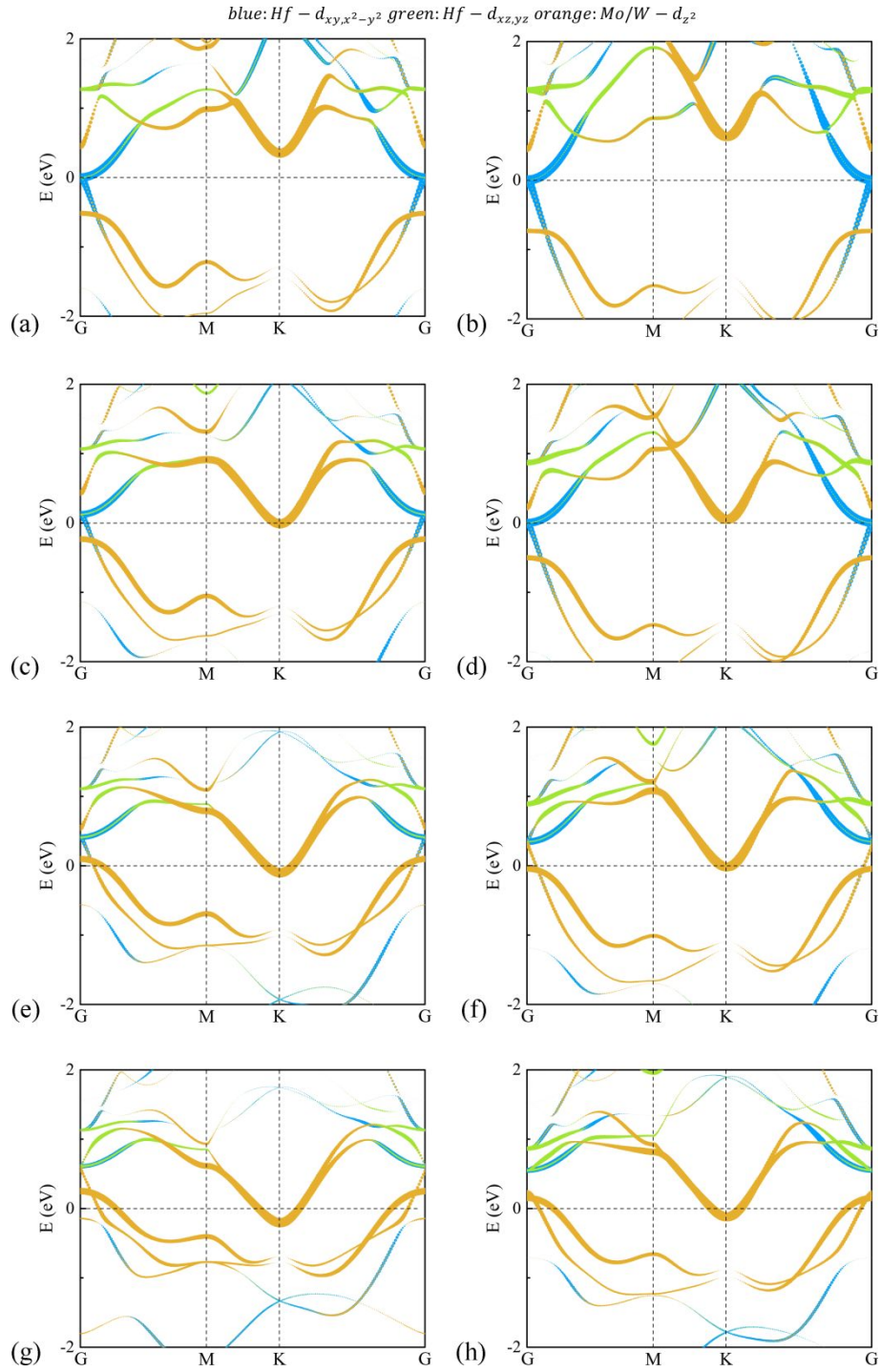


Figure S9. Projected band structures of $Mo_2HfC_2O_2$ (a) in equilibrium, (c) at strain $\varepsilon = 5\%$, (e) at strain $\varepsilon = 10\%$, and (g) at strain $\varepsilon = 15\%$. Projected band structures of $W_2HfC_2O_2$ (b) in equilibrium, (d) at strain $\varepsilon = 5\%$, (f) at strain $\varepsilon = 10\%$, and (h) at strain $\varepsilon = 15\%$. The Fermi level is set to zero energy.

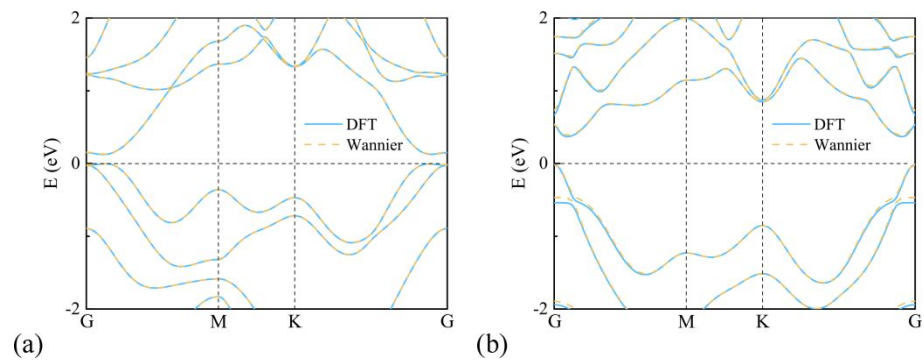


Figure S10. The fitted band structures to DFT and MLWFs for (a) $\text{Mo}_2\text{TiC}_2\text{O}_2$ and (b) $\text{W}_2\text{HfC}_2\text{O}_2$.

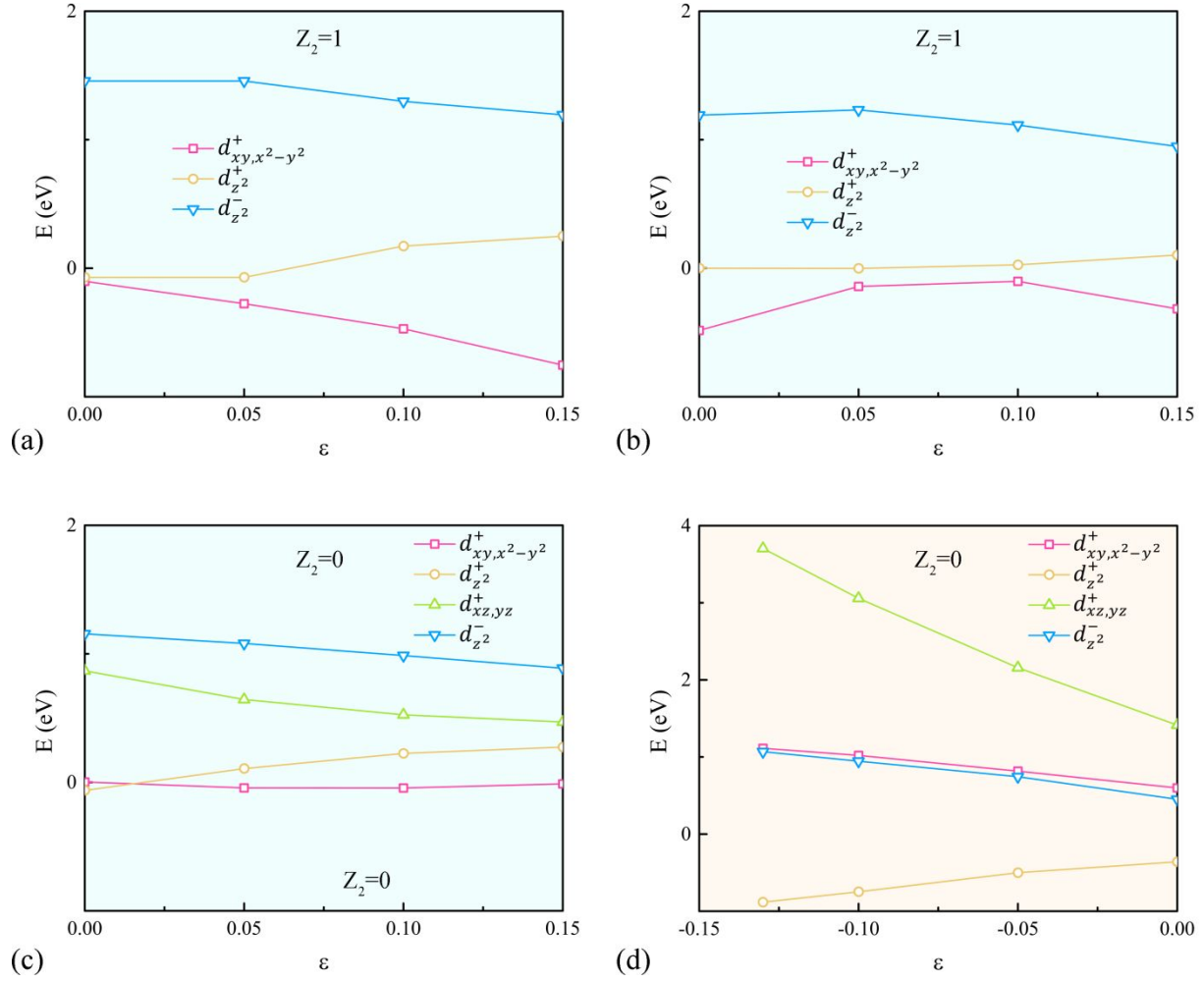


Figure S11. Energy levels of $|M'' - d_{z^2}^\pm\rangle$, $|M'' - d_{xy,x^2-y^2}^+\rangle$, and $|M'' - d_{z^2}^\pm\rangle$ states at Γ point vs strain ε curves of (a) Mo_2CO_2 and (b) W_2CO_2 . Energy levels of $|M'' - d_{z^2}^\pm\rangle$, $|M' - d_{xy,x^2-y^2}^+\rangle$, $|M' - d_{xz,yz}^+\rangle$ and $|M'' - d_{z^2}^\pm\rangle$ states at Γ point vs strain ε curves of (c) $\text{Mo}_2\text{Ti}_2\text{C}_3\text{O}_2$ and (d) $\text{W}_2\text{Hf}_2\text{C}_3\text{O}_2$. Note that a compression strain is adopted in $\text{W}_2\text{Hf}_2\text{C}_3\text{O}_2$, different from the tensile strain in the others.

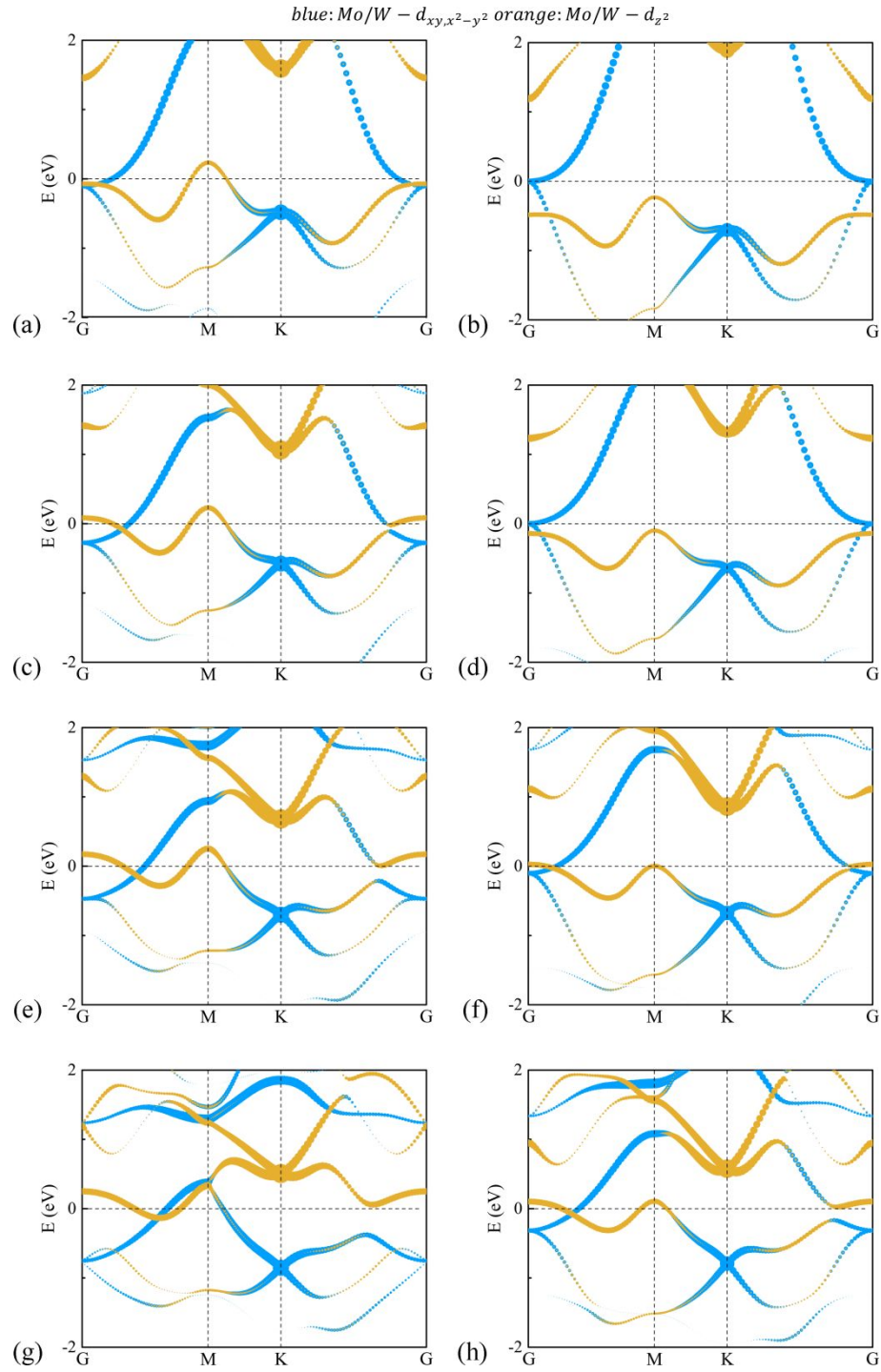


Figure S12. Projected band structures of Mo_2CO_2 (a) in equilibrium, (c) at strain $\varepsilon = 5\%$, (e) at strain $\varepsilon = 10\%$, and (g) at strain $\varepsilon = 15\%$. Projected band structures of W_2CO_2 (b) in equilibrium, (d) at strain $\varepsilon = 5\%$, (f) at strain $\varepsilon = 10\%$, and (h) at strain $\varepsilon = 15\%$. The Fermi level is set to zero energy.

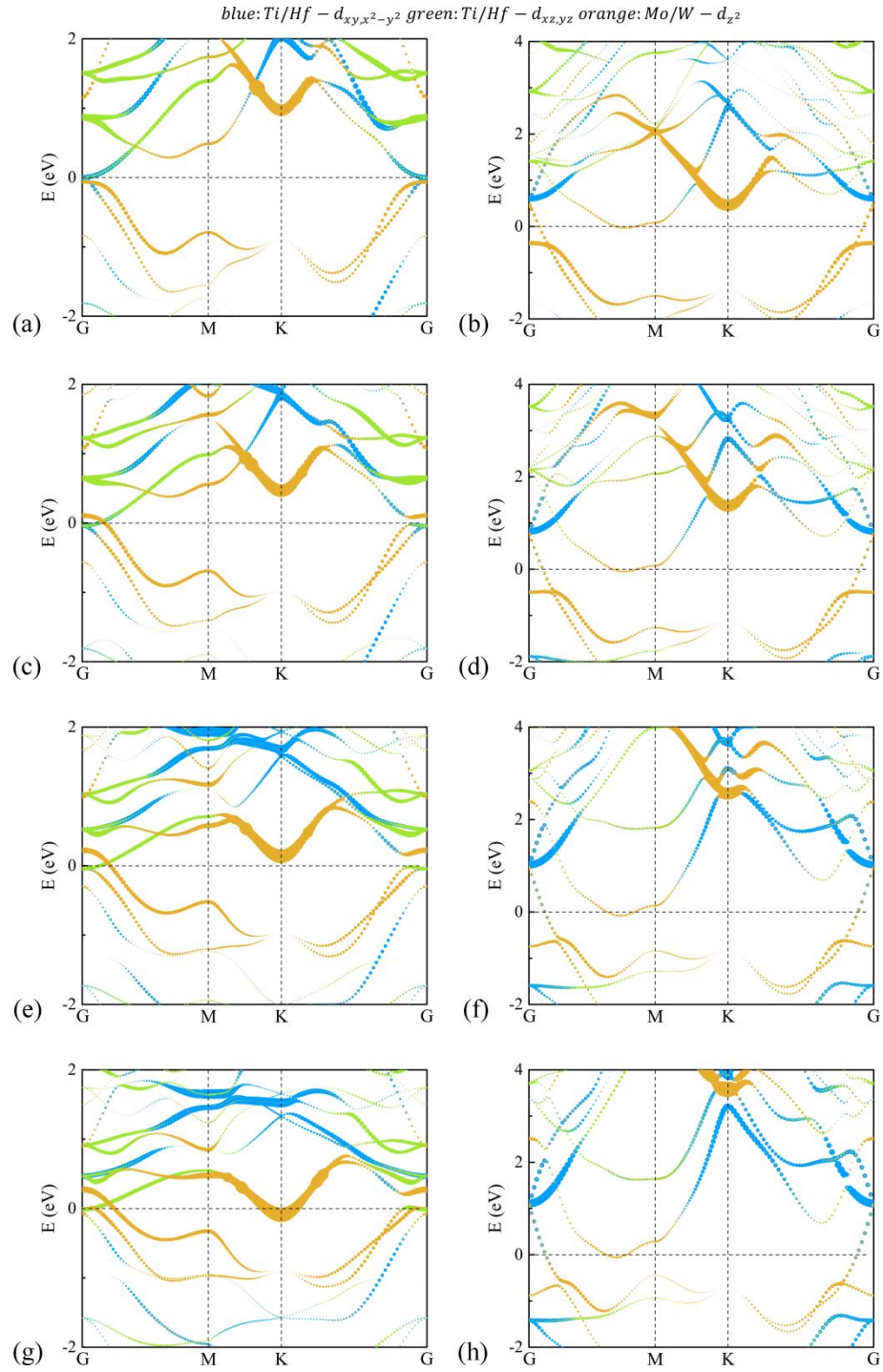


Figure S13. Projected band structures of $\text{Mo}_2\text{Ti}_2\text{C}_3\text{O}_2$ (a) in equilibrium, (c) at strain $\varepsilon = 5\%$, (e) at strain $\varepsilon = 10\%$, and (g) at strain $\varepsilon = 15\%$. Projected band structures of $\text{W}_2\text{Hf}_2\text{C}_3\text{O}_2$ (b) in equilibrium, (d) at strain $\varepsilon = -5\%$, (f) at strain $\varepsilon = -10\%$, and (h) at strain $\varepsilon = -15\%$ (the symbol “-” represents the compression strain). The Fermi level is set to zero energy.

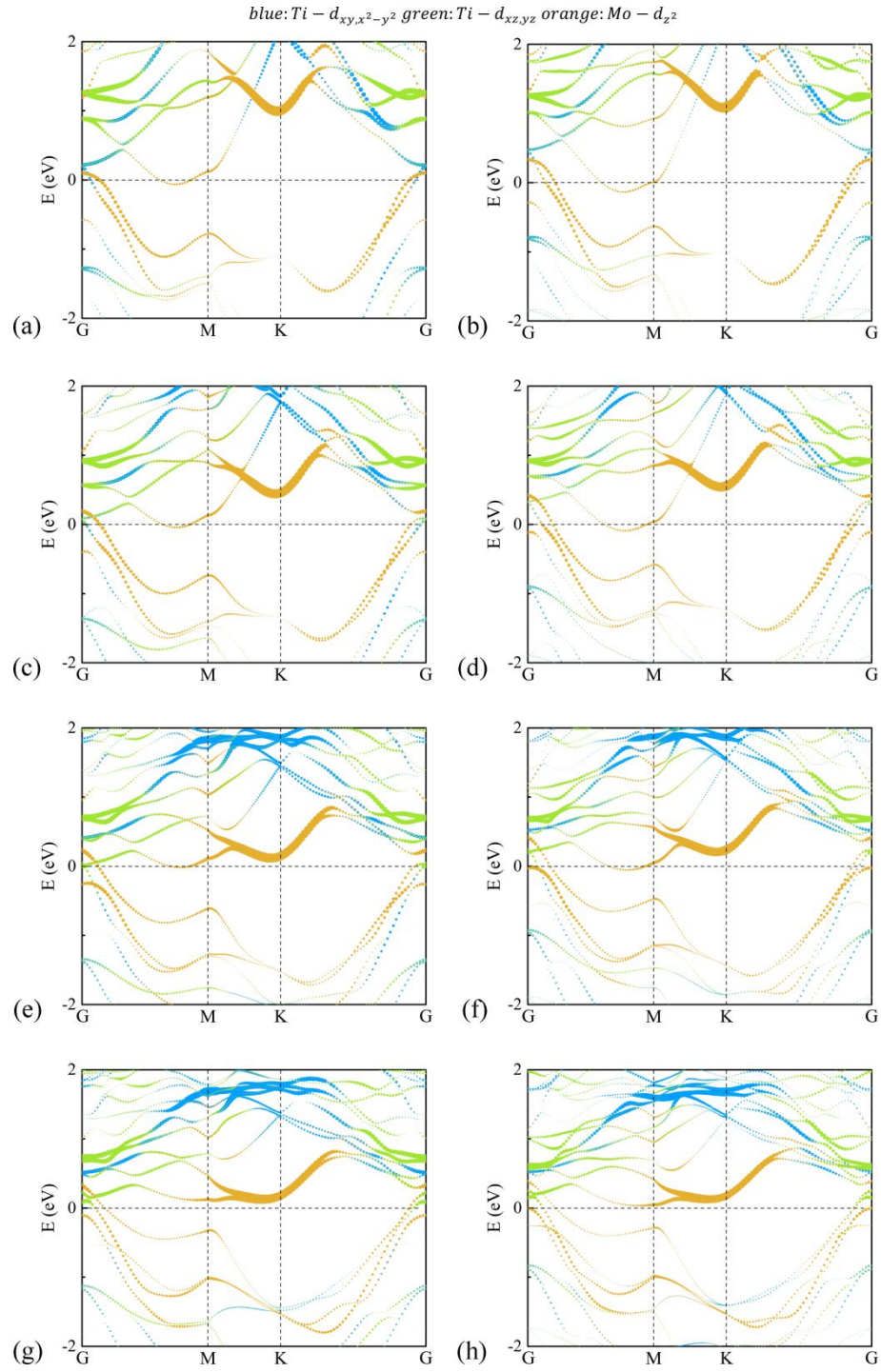


Figure S14. Projected band structures of $Mo_2Ti_3C_4O_2$ (a) in equilibrium, (c) at strain $\varepsilon = 5\%$, (e) at strain $\varepsilon = 10\%$, and (g) at strain $\varepsilon = 15\%$. Projected band structures of $Mo_2Ti_4C_5O_2$ (b) in equilibrium, (d) at strain $\varepsilon = 5\%$, (f) at strain $\varepsilon = 10\%$, and (h) at strain $\varepsilon = 15\%$. The Fermi level is set to zero energy.

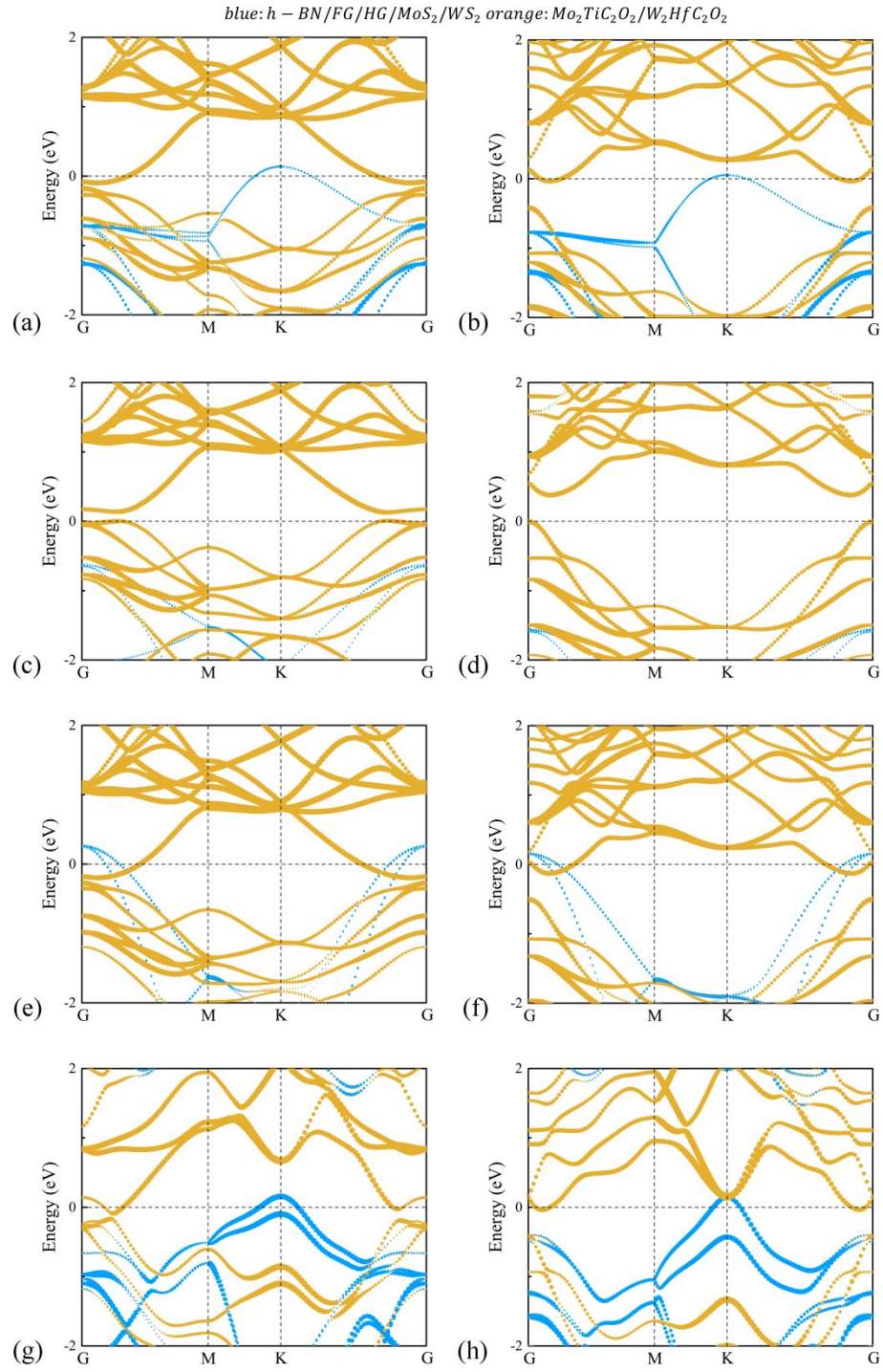


Figure S15. Atomic projected band structures of Mo₂TiC₂O₂ with large-gap coating layer (a) h-BN, (c) fluorographene, (e) graphane, (g) MoS₂. Atomic projected band structures of W₂HfC₂O₂ with large-gap coating layer (b) h-BN, (d) fluorographene, (f) graphane, (h) WS₂. The Fermi level is set to zero energy.

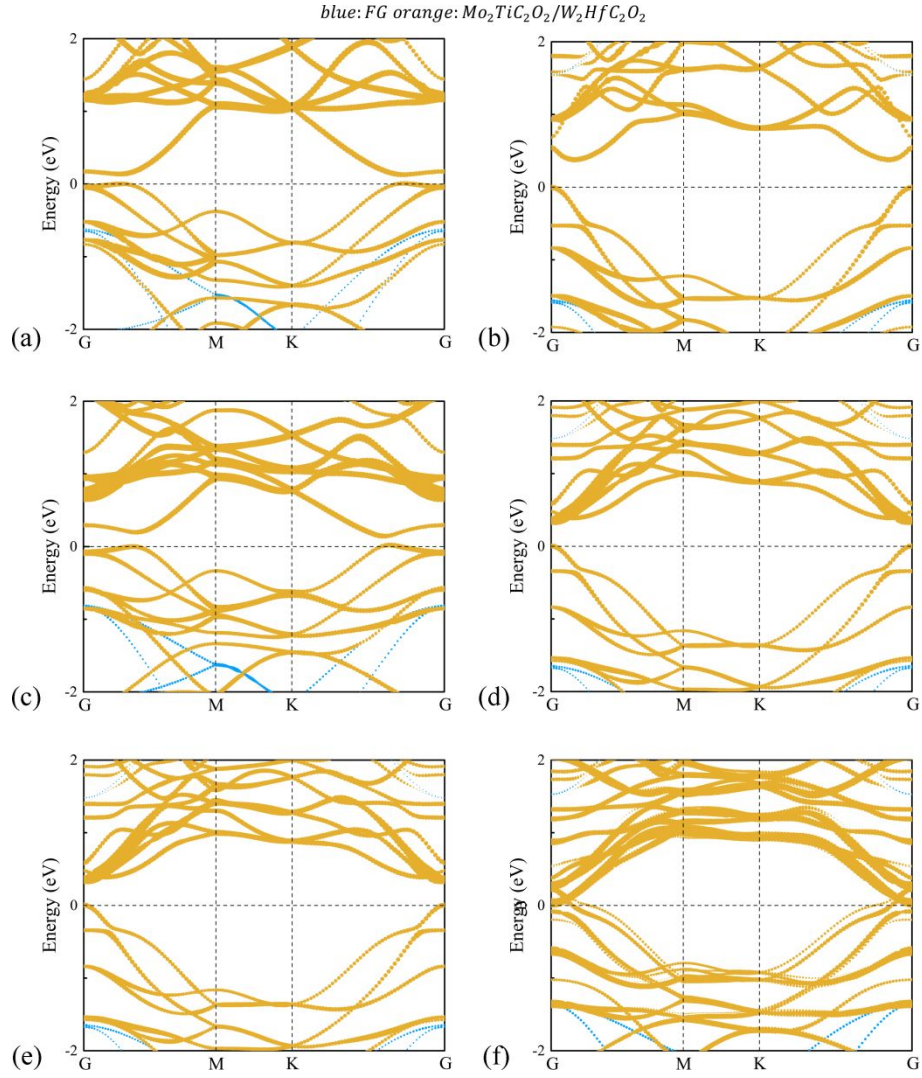


Figure S16. Atomic projected band structures of $\text{Mo}_2\text{TiC}_2\text{O}_2$ with large-gap coating layer fluorographene (a) in equilibrium, (c) at strain $\varepsilon = 5\%$, and (e) at strain $\varepsilon = 10\%$. Atomic projected band structures of $\text{W}_2\text{HfC}_2\text{O}_2$ with large-gap coating layer fluorographene (b) in equilibrium, (d) at strain $\varepsilon = 5\%$, and (f) at strain $\varepsilon = 10\%$. The Fermi level is set to zero energy.